

# BLF7G27L-100; BLF7G27LS-100

Power LDMOS transistor

Rev. 3 — 22 July 2011

Product data sheet

## 1. Product profile

### 1.1 General description

100 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

**Table 1. Typical performance**

Typical RF performance at  $T_{case} = 25\text{ }^{\circ}\text{C}$  in a common source class-AB production test circuit.

| Mode of operation     | f<br>(MHz)   | $I_{DQ}$<br>(mA) | $V_{DS}$<br>(V) | $P_{L(AV)}$<br>(W) | $G_p$<br>(dB) | $\eta_D$<br>(%) | $ACPR_{885k}$<br>(dBc) | $ACPR_{5M}$<br>(dBc) |
|-----------------------|--------------|------------------|-----------------|--------------------|---------------|-----------------|------------------------|----------------------|
| IS-95                 | 2500 to 2700 | 900              | 28              | 20                 | 18            | 28              | -45 <sup>[1]</sup>     | -                    |
| Single carrier W-CDMA | 2500 to 2700 | 900              | 28              | 25                 | 17.5          | 30              | -                      | -41 <sup>[2]</sup>   |

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

[2] 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.

### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low  $R_{th}$  providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

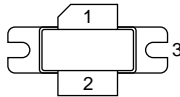
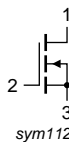
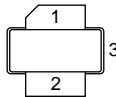
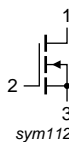
### 1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range.



## 2. Pinning information

Table 2. Pinning

| Pin                     | Description | Simplified outline  | Graphic symbol  |
|-------------------------|-------------|---|---|
| BLF7G27L-100 (SOT502A)  |             |   |   |
| 1                       | drain       |  |  |
| 2                       | gate        |   |   |
| 3                       | source      |   |   |
| BLF7G27LS-100 (SOT502B) |             |   |   |
| 1                       | drain       |  |  |
| 2                       | gate        |   |   |
| 3                       | source      |   |   |

[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

| Type number   | Package |   |         |
|---------------|---------|---|---------|
|               | Name    | Description   | Version |
| BLF7G27L-100  | -       | flanged LDMOST ceramic package; 2 mounting holes; 2 leads | SOT502A |
| BLF7G27LS-100 | -       | earless flanged LDMOST ceramic package; 2 leads           | SOT502B |

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter            | Conditions | Min  | Max  | Unit |
|-----------|----------------------|------------|------|------|------|
| $V_{DS}$  | drain-source voltage |            | -    | 65   | V    |
| $V_{GS}$  | gate-source voltage  |            | -0.5 | +13  | V    |
| $I_D$     | drain current        |            | -    | 28   | A    |
| $T_{stg}$ | storage temperature  |            | -65  | +150 | °C   |
| $T_j$     | junction temperature |            | -    | 200  | °C   |

## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol        | Parameter                                | Conditions                                       | Typ  | Unit |
|---------------|--|--|------|------|
| $R_{th(j-c)}$ | thermal resistance from junction to case | $T_{case} = 80\text{ °C}$ ; $P_L = 100\text{ W}$ | 0.25 | K/W  |

## 6. Characteristics

**Table 6. Characteristics**

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

| Symbol        | Parameter                        | Conditions  | Min  | Typ  | Max | Unit          |
|---------------|----------------------------------|---|------|------|-----|---------------|
| $V_{(BR)DSS}$ | drain-source breakdown voltage   | $V_{GS} = 0\text{ V}$ ; $I_D = 1\text{ mA}$                       | 65   | -    | -   | V             |
| $V_{GS(th)}$  | gate-source threshold voltage    | $V_{DS} = 10\text{ V}$ ; $I_D = 153\text{ mA}$                    | 1.5  | 1.8  | 2.3 | V             |
| $I_{DSS}$     | drain leakage current            | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 28\text{ V}$                    | -    | -    | 5   | $\mu\text{A}$ |
| $I_{DSX}$     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75\text{ V}$ ;<br>$V_{DS} = 10\text{ V}$ | 25.1 | 29   | -   | A             |
| $I_{GSS}$     | gate leakage current             | $V_{GS} = 11\text{ V}$ ; $V_{DS} = 0\text{ V}$                    | -    | -    | 500 | nA            |
| $g_{fs}$      | forward transconductance         | $V_{DS} = 10\text{ V}$ ; $I_D = 153\text{ mA}$                    | -    | 1.34 | -   | S             |
| $R_{DS(on)}$  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75\text{ V}$ ;<br>$I_D = 5.35\text{ A}$  | -    | 0.1  | -   | $\Omega$      |

## 7. Test information

**Remark:** All testing performed in a class-AB production test circuit.

**Table 7. Functional test information**

Mode of operation: 1-carrier N-CDMA, single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz;  $f_1 = 2500\text{ MHz}$ ;  $f_2 = 2700\text{ MHz}$ ; RF performance at  $V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 900\text{ mA}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ; unless otherwise specified.

| Symbol        | Parameter                              | Conditions | Min  | Typ | Max | Unit |
|---------------|--|------------|------|-----|-----|------|
| $P_{L(AV)}$   | average output power                   |            | -    | 20  | -   | W    |
| $G_p$         | power gain                             |            | 16.3 | 18  | -   | dB   |
| $RL_{in}$     | input return loss                      |            | -    | -10 | -   | dB   |
| $\eta_D$      | drain efficiency                       |            | 24   | 28  | -   | %    |
| $ACPR_{885k}$ | adjacent channel power ratio (885 kHz) |            | -    | -45 | -40 | dBc  |

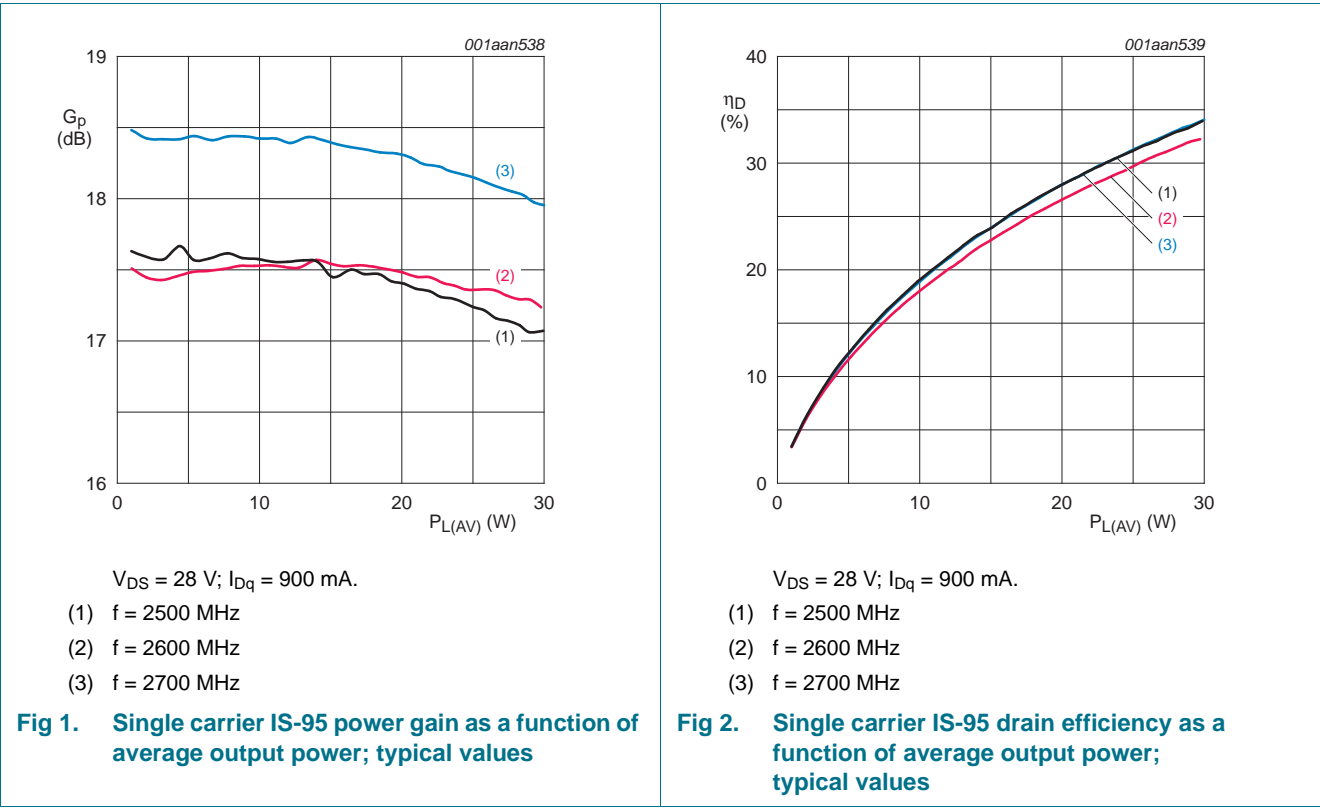
### 7.1 Ruggedness in class-AB operation

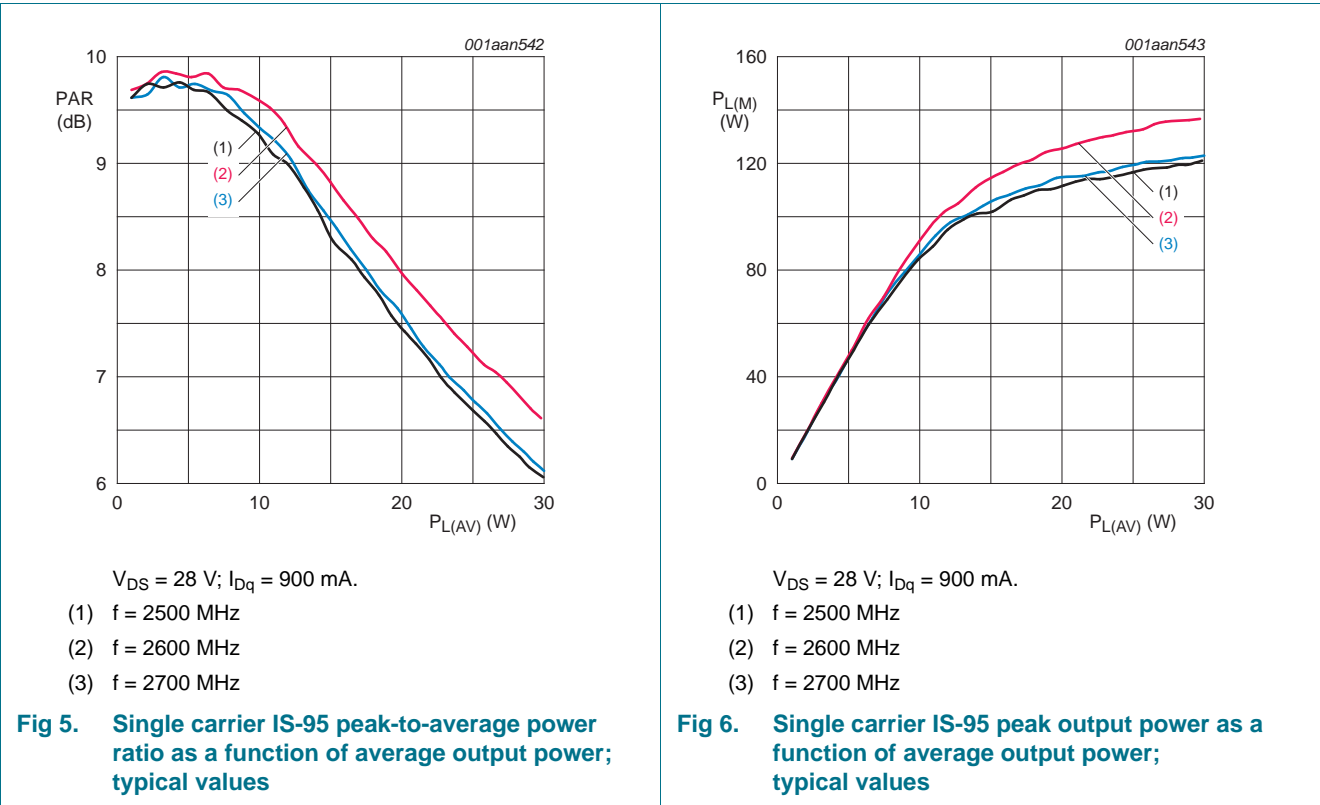
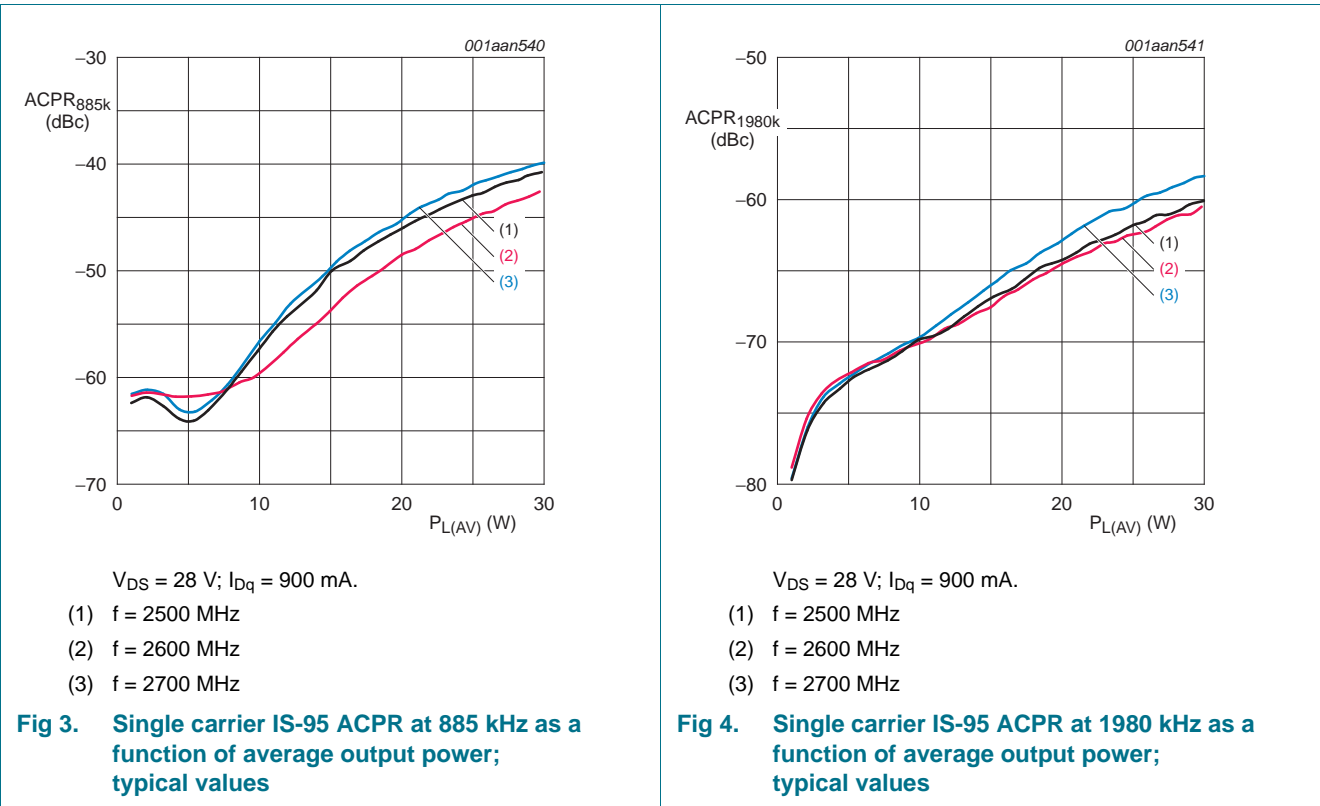
The BLF7G27L-100 and BLF7G27LS-100 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:

$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 900\text{ mA}$ ;  $P_L = 100\text{ W}$  (CW);  $f = 2500\text{ MHz}$ .

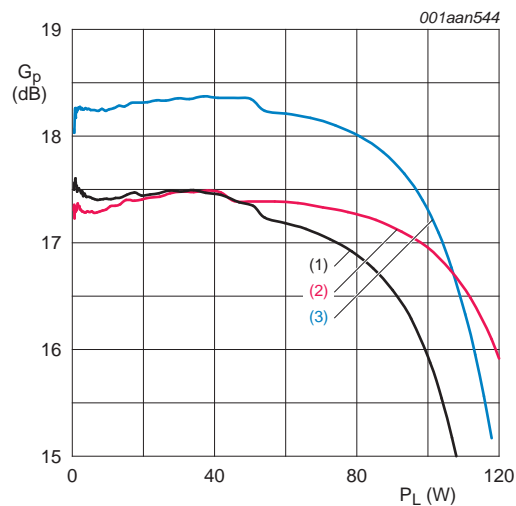
7.2 Single carrier IS-95

Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13).  
PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.





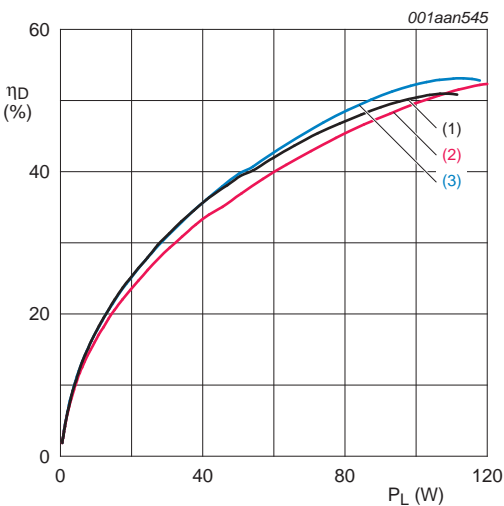
7.3 Pulsed CW



$V_{DS} = 28$  V;  $I_{DQ} = 900$  mA.

- (1)  $f = 2500$  MHz
- (2)  $f = 2600$  MHz
- (3)  $f = 2700$  MHz

Fig 7. Pulsed CW power gain as a function of output power; typical values



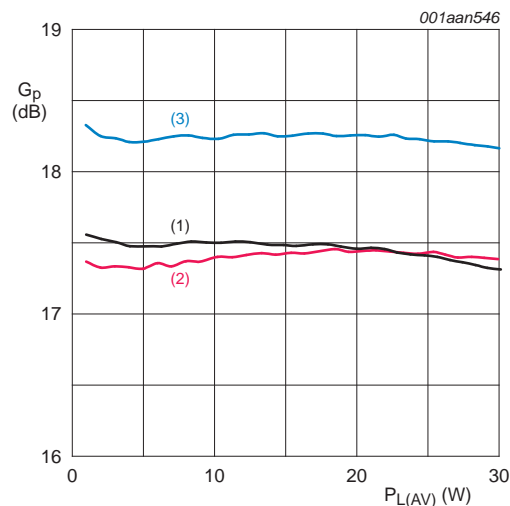
$V_{DS} = 28$  V;  $I_{DQ} = 900$  mA.

- (1)  $f = 2500$  MHz
- (2)  $f = 2600$  MHz
- (3)  $f = 2700$  MHz

Fig 8. Pulsed CW drain efficiency as a function of output power; typical values

7.4 Single carrier W-CDMA

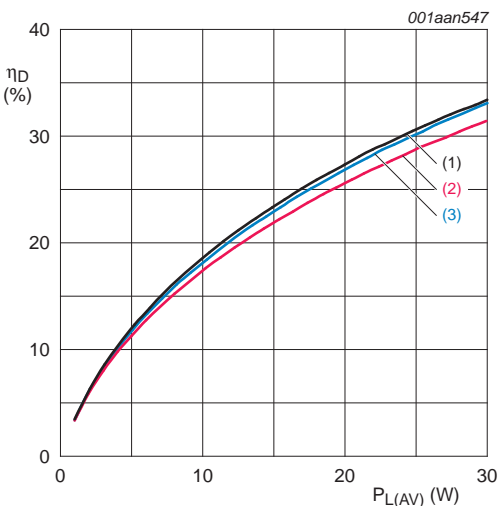
3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.  
Channel bandwidth is 3.84 MHz.



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

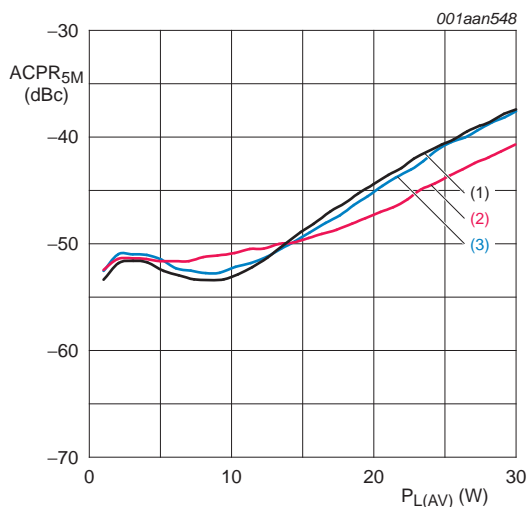
Fig 9. Single carrier W-CDMA power gain as a function of average output power; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

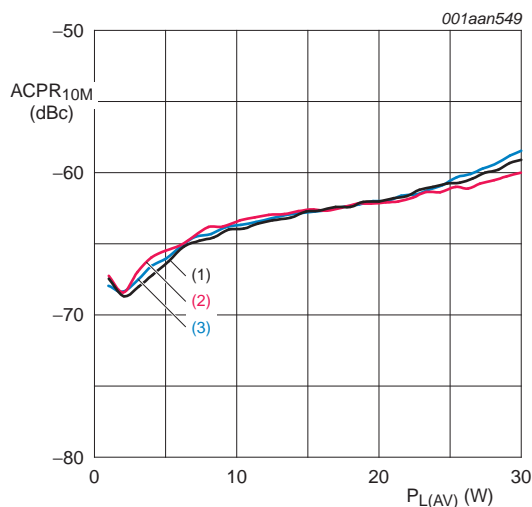
Fig 10. Single carrier W-CDMA drain efficiency as a function of average output power; typical values



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

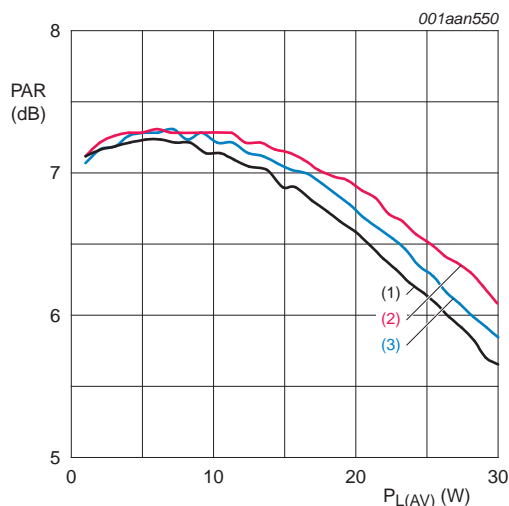
**Fig 11. Single carrier W-CDMA ACPR at 5 MHz as a function of average output power; typical values**



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

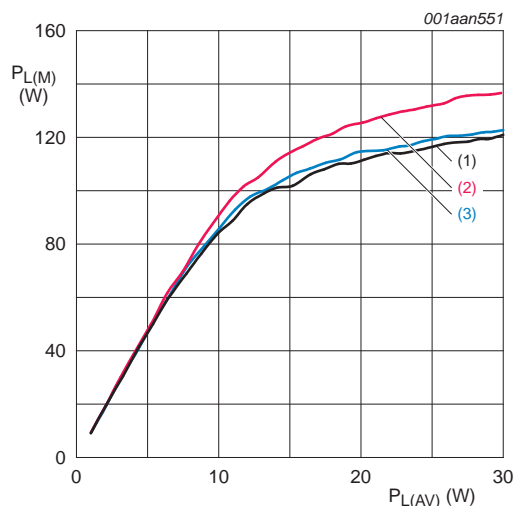
**Fig 12. Single carrier W-CDMA ACPR at 10 MHz as a function of average output power; typical values**



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

**Fig 13. Single carrier W-CDMA peak-to-average power ratio as a function of average output power; typical values**



$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 900\text{ mA}$ .

- (1)  $f = 2500\text{ MHz}$
- (2)  $f = 2600\text{ MHz}$
- (3)  $f = 2700\text{ MHz}$

**Fig 14. Single carrier W-CDMA peak output power as a function of average output power; typical values**



8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A

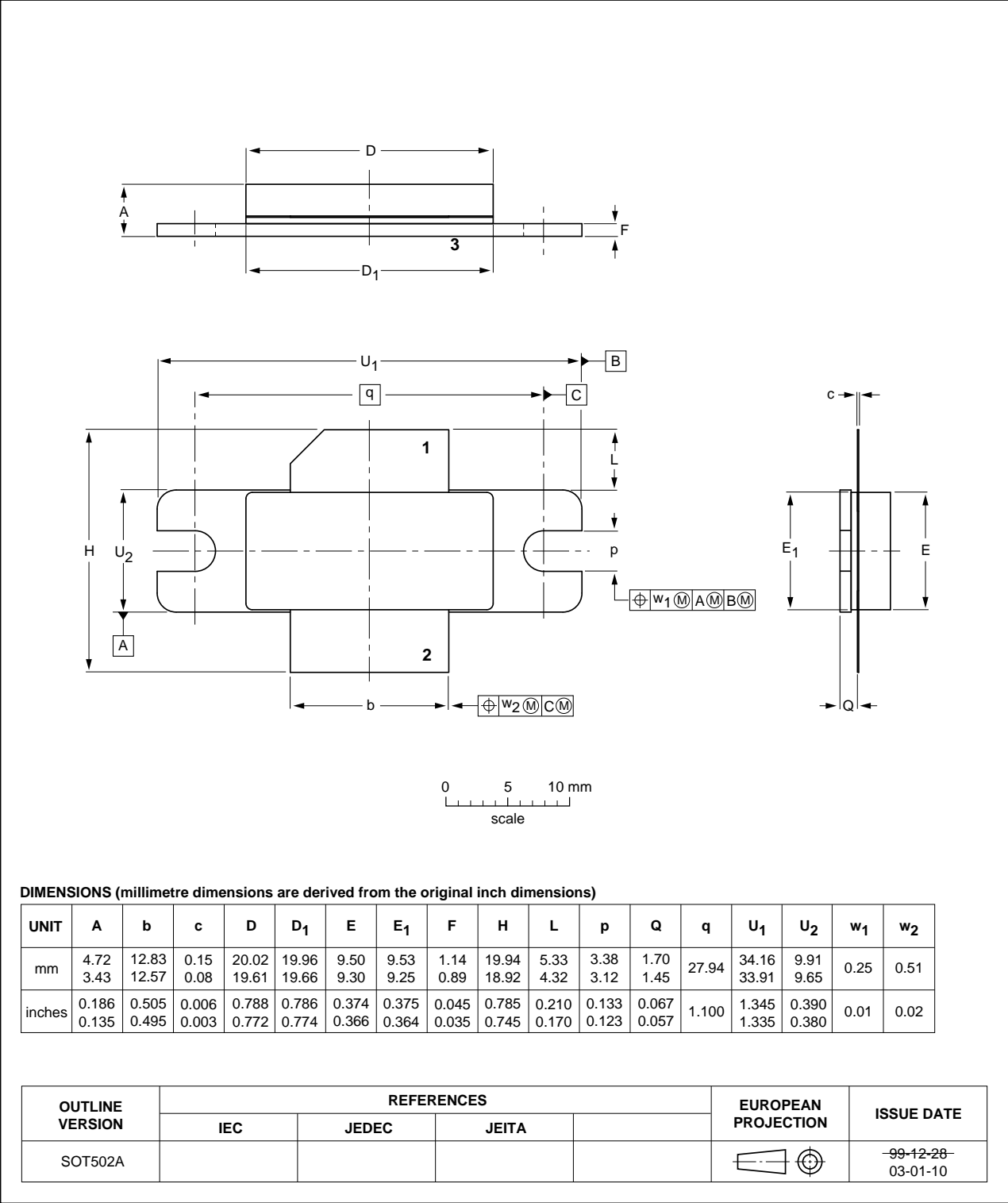
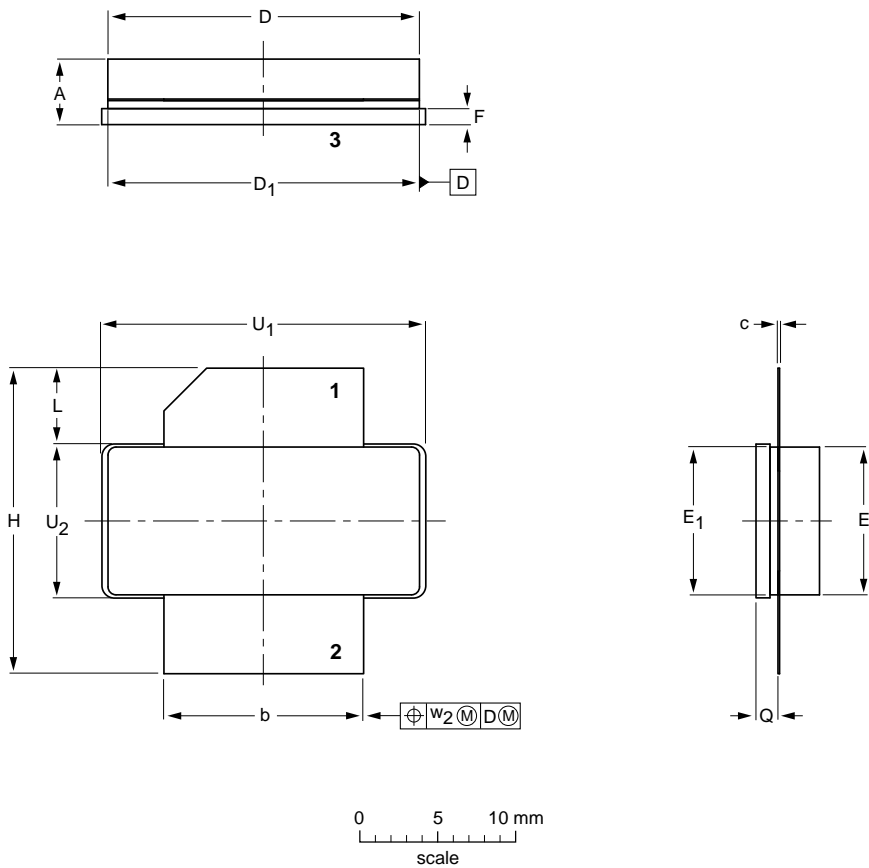


Fig 15. Package outline SOT502A

Earless flanged LDMOST ceramic package; 2 leads

SOT502B



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

| UNIT   | A              | b              | c              | D              | D <sub>1</sub> | E              | E <sub>1</sub> | F              | H              | L              | Q              | U <sub>1</sub> | U <sub>2</sub> | w <sub>2</sub> |
|--------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|----------------|
| mm     | 4.72<br>3.43   | 12.83<br>12.57 | 0.15<br>0.08   | 20.02<br>19.61 | 19.96<br>19.66 | 9.50<br>9.30   | 9.53<br>9.25   | 1.14<br>0.89   | 19.94<br>18.92 | 5.33<br>4.32   | 1.70<br>1.45   | 20.70<br>20.45 | 9.91<br>9.65   | 0.25           |
| inches | 0.186<br>0.135 | 0.505<br>0.495 | 0.006<br>0.003 | 0.788<br>0.772 | 0.786<br>0.774 | 0.374<br>0.366 | 0.375<br>0.364 | 0.045<br>0.035 | 0.785<br>0.745 | 0.210<br>0.170 | 0.067<br>0.057 | 0.815<br>0.805 | 0.390<br>0.380 | 0.010          |

| OUTLINE<br>VERSION | REFERENCES |       |       |  | EUROPEAN<br>PROJECTION | ISSUE DATE            |
|--------------------|------------|-------|-------|--|------------------------|-----------------------|
|                    | IEC        | JEDEC | JEITA |  |                        |                       |
| SOT502B            |            |       |       |  |                        | 03-01-10-<br>07-05-09 |

Fig 16. Package outline SOT502B

## 9. Abbreviations

Table 8. Abbreviations

| Acronym | Description   |
|---------|---|
| 3GPP    | Third Generation Partnership Project                    |
| CCDF    | Complementary Cumulative Distribution Function          |
| CW      | Continuous Wave   |
| DPCH    | Dedicated Physical CHannel                              |
| IS-95   | Interim Standard 95                                     |
| ESD     | ElectroStatic Discharge                                 |
| LDMOS   | Laterally Diffused Metal Oxide Semiconductor            |
| LDMOST  | Laterally Diffused Metal Oxide Semiconductor Transistor |
| N-CDMA  | Narrowband Code Division Multiple Access                |
| PAR     | Peak-to-Average power Ratio                             |
| RF      | Radio Frequency   |
| VSWR    | Voltage Standing Wave Ratio                             |

## 10. Revision history

Table 9. Revision history

| Document ID                 | Release date | Data sheet status  | Change notice | Supersedes                  |
|-----------------------------|--------------|--|---------------|-----------------------------|
| BLF7G27L-100_7G27LS-100 v.3 | 20110722     | Product data sheet   | -             | BLF7G27L-100_7G27LS-100 v.2 |
| Modifications:              |              | • The status of this data sheet has been changed to Product data sheet |               |                             |
| BLF7G27L-100_7G27LS-100 v.2 | 20110405     | Preliminary data sheet   | -             | BLF7G27L-100_7G27LS-100 v.1 |
| BLF7G27L-100_7G27LS-100 v.1 | 20100421     | Objective data sheet   | -             | -                           |

## 11. Legal information

### 11.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

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[2] The term 'short data sheet' is explained in section "Definitions".

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